

ABSTRACT OF THE DISCLOSURE

A semiconductor device which can suppress an electric breakdown. In the semiconductor device, a base electrode is connected to a base region in a base contact region defined on a surface of the base region. An N-type region having the same conductivity type as an emitter region is provided beneath a boundary portion of the base contact region to surround the base contact region. In other words, a PN-type diode constituted by the P-type base region and the N-type region is provided beneath the boundary portion of the base contact region.